

PMCM440VNE

12 V, N-channel Trench MOSFET

7 April 2015

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a 4 bumps Wafer Level Chip-Size Package (WLCSP) using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Ultra small package: 0.78 × 0.78 × 0.35 mm
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ °C}$	-	-	12	V
V_{GS}	gate-source voltage		-8	-	8	V
I_D	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ °C}; t \leq 5\text{ s}$	[1]	-	5	A
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 3\text{ A}; T_j = 25\text{ °C}$	-	57	67	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

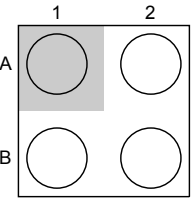
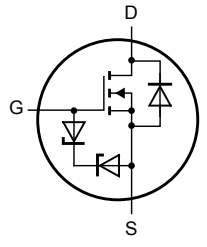


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
A1	G	gate	 <p>Transparent top view WLCSP4 (OL-PMCM440VNE)</p>	 <p>017aaa255</p>
A2	S	source		
B1	D	drain		
B2	S	source		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMCM440VNE	WLCSP4	WLCSP4: wafer level chip-size package; 4 bumps (2 x 2)	OL-PMCM440VNE

7. Marking

Table 4. Marking codes

Type number	Marking code
PMCM440VNE	M

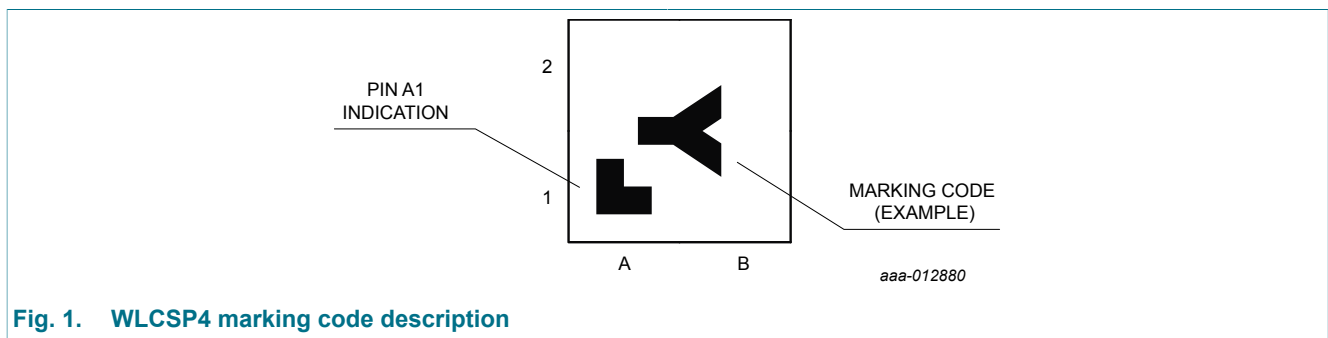


Fig. 1. WLCSP4 marking code description

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ °C}$		-	12	V
V_{GS}	gate-source voltage			-8	8	V
I_D	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ °C}; t \leq 5\text{ s}$	[1]	-	5	A
		$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	3.9	A
		$V_{GS} = 4.5\text{ V}; T_{amb} = 100\text{ °C}$	[1]	-	15.5	A
I_{DM}	peak drain current	$T_{amb} = 25\text{ °C}; \text{single pulse}; t_p \leq 10\text{ }\mu\text{s}$		-	16	A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ °C}$	[2]	-	400	mW
			[1]	-	1300	mW
		$T_{sp} = 25\text{ °C}$		-	12500	mW
T_j	junction temperature			-55	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C
Source-drain diode						
I_S	source current	$T_{amb} = 25\text{ °C}$	[1]	-	1.1	A

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm^2 .
- [2] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

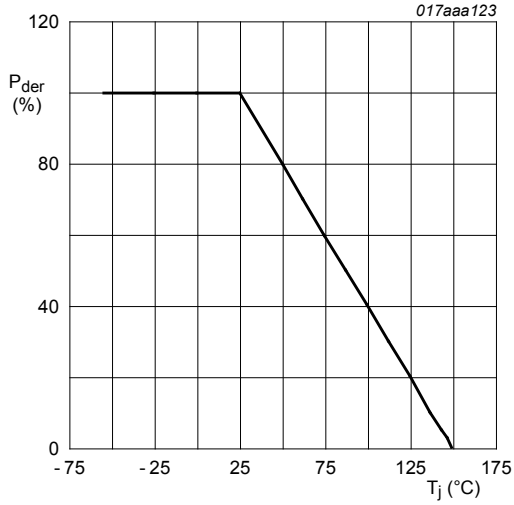


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \%$$

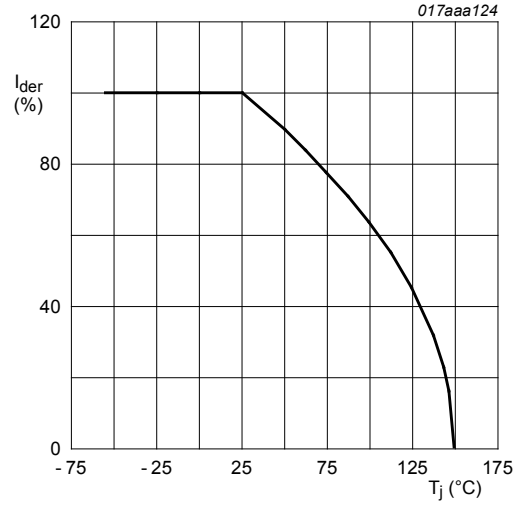
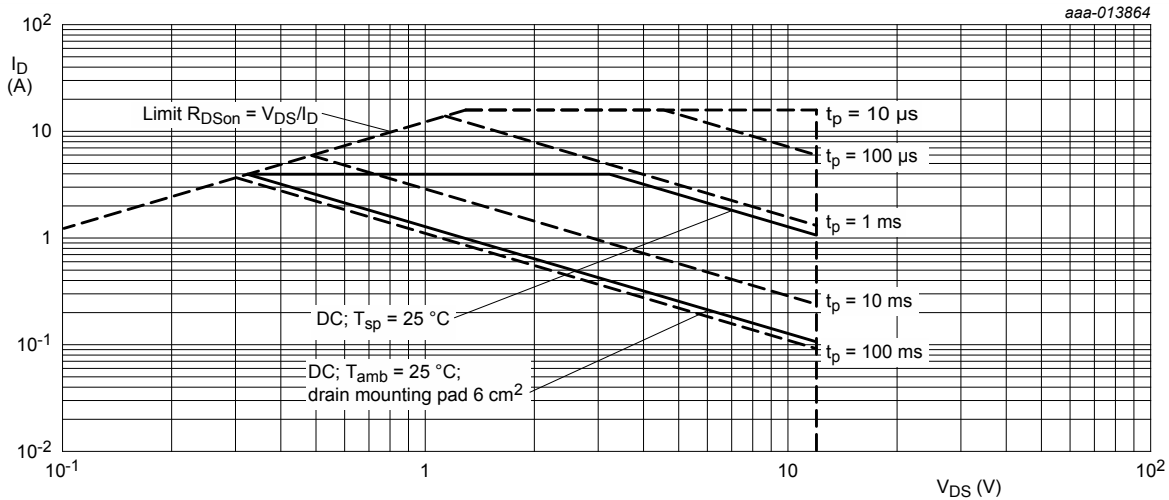


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$



I_{DM} = single pulse

Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	250	300	K/W
			[2]	-	70	85	K/W
			[3]	-	85	100	K/W
		in free air; t ≤ 5 s	[3]	-	50	60	K/W

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	5	10	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain, 4-layer, 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

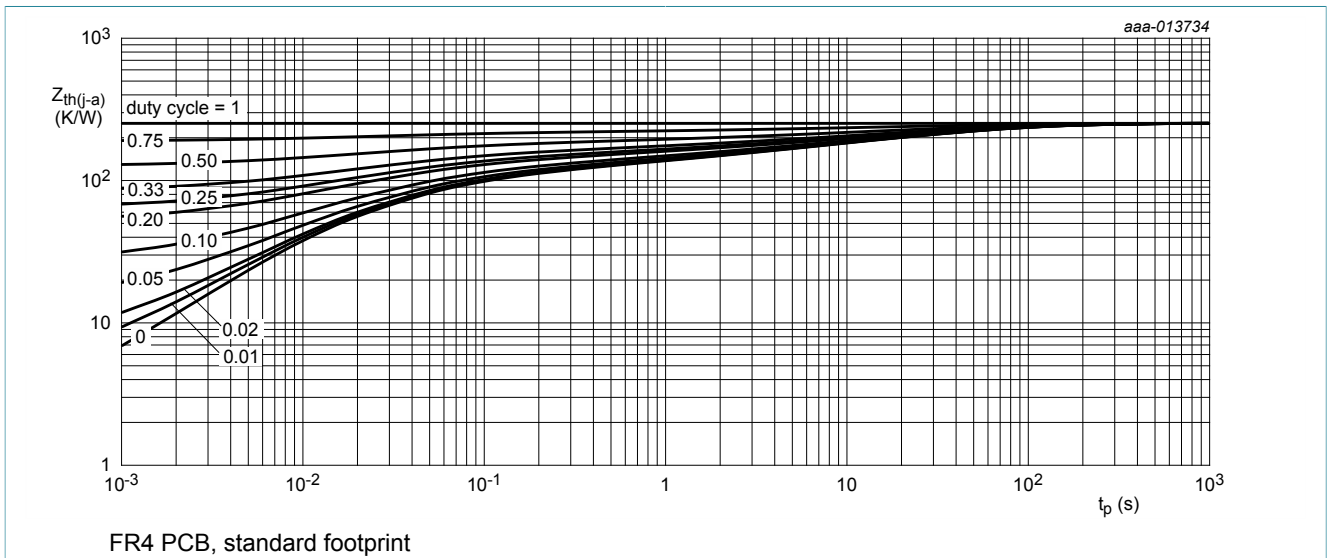


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

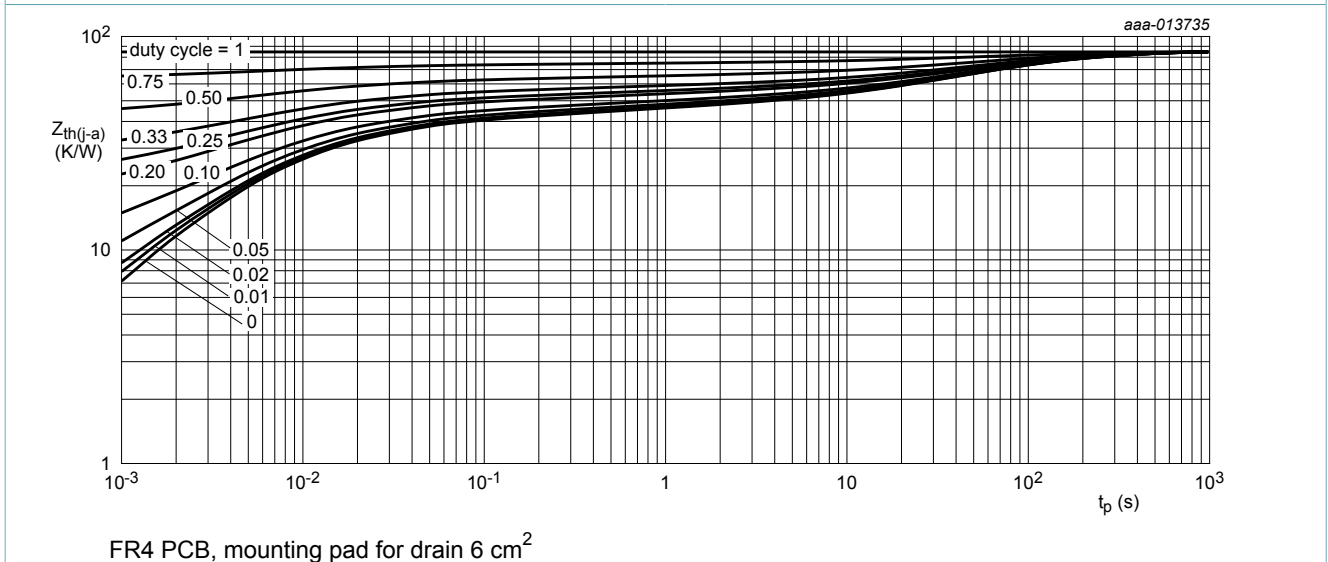


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	12	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	0.4	0.6	0.9	V
I_{DSS}	drain leakage current	$V_{DS} = 12 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	μA
I_{GSS}	gate leakage current	$V_{GS} = 8 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	10	μA
		$V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-10	μA
		$V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	5	μA
		$V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-5	μA
		$V_{GS} = 2.5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	200	nA
		$V_{GS} = -2.5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-200	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 V; I_D = 3 A; T_j = 25 \text{ }^\circ C$	-	57	67	m Ω
		$V_{GS} = 4.5 V; I_D = 3 A; T_j = 150 \text{ }^\circ C$	-	71	83	m Ω
		$V_{GS} = 2.5 V; I_D = 3 A; T_j = 25 \text{ }^\circ C$	-	66	88	m Ω
		$V_{GS} = 1.8 V; I_D = 1 A; T_j = 25 \text{ }^\circ C$	-	77	110	m Ω
		$V_{GS} = 1.5 V; I_D = 0.1 A; T_j = 25 \text{ }^\circ C$	-	90	130	m Ω
g_{fs}	forward transconductance	$V_{DS} = 6 V; I_D = 3 A; T_j = 25 \text{ }^\circ C$	-	17	-	S
R_G	gate resistance	$f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$	-	5.4	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 6 V; I_D = 3 A; V_{GS} = 4.5 V; T_j = 25 \text{ }^\circ C$	-	5.5	8.2	nC
Q_{GS}	gate-source charge		-	0.43	-	nC
Q_{GD}	gate-drain charge		-	1.5	-	nC
C_{iss}	input capacitance	$V_{DS} = 6 V; f = 1 \text{ MHz}; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	360	-	pF
C_{oss}	output capacitance		-	160	-	pF
C_{riss}	reverse transfer capacitance		-	140	-	pF
$t_{d(on)}$	turn-on delay time		$V_{DS} = 6 V; I_D = 3 A; V_{GS} = 4.5 V; R_{G(ext)} = 6 \Omega; T_j = 25 \text{ }^\circ C$	-	6.3	-
t_r	rise time	-		24	-	ns
$t_{d(off)}$	turn-off delay time	-		27	-	ns
t_f	fall time	-		17	-	ns

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 1.1 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.7	1.2	V

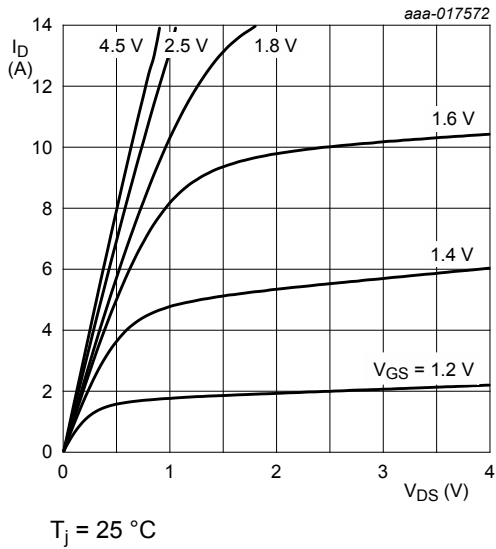


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

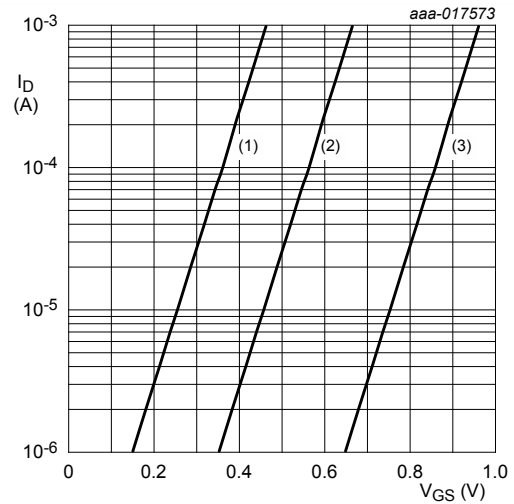


Fig. 8. Sub-threshold drain current as a function of gate-source voltage
 $T_j = 25 \text{ }^\circ\text{C}; V_{DS} = 5 \text{ V}$
 (1) minimum values
 (2) typical values
 (3) maximum values

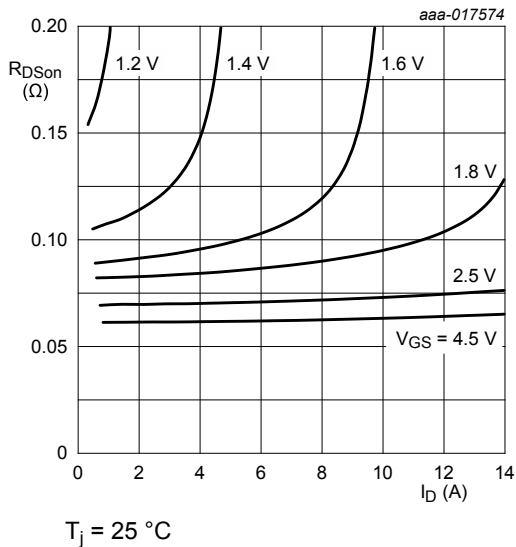


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

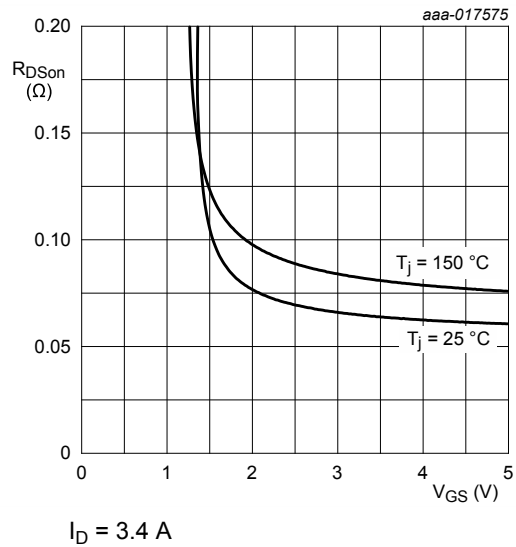
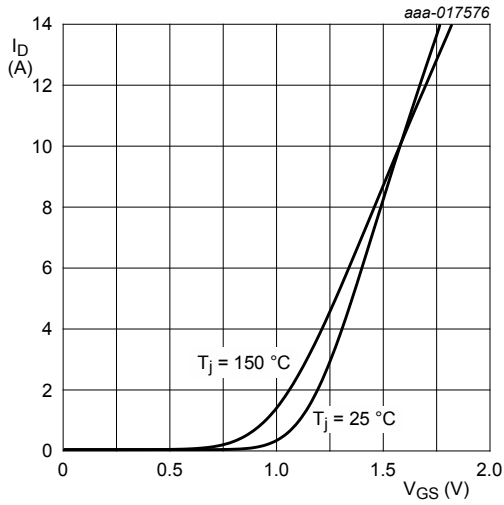


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values



$$V_{DS} > I_D \times R_{DS(on)}$$

Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

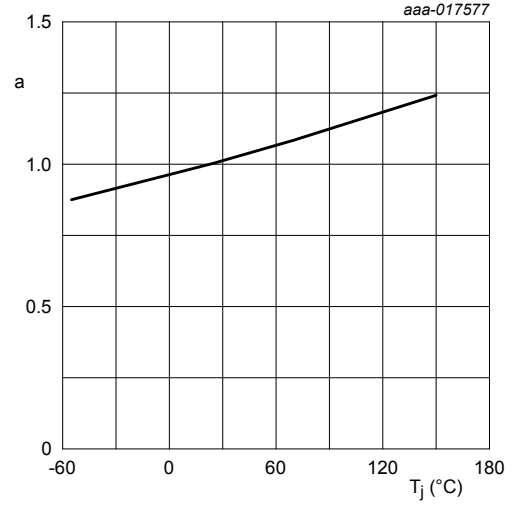
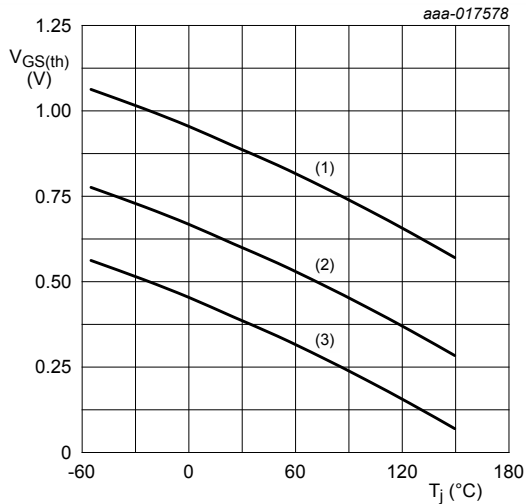


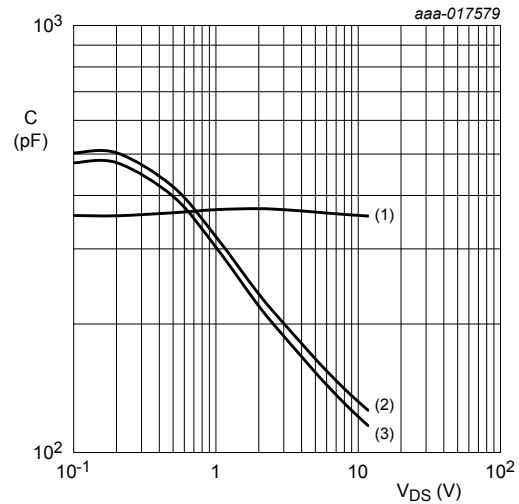
Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DS(on)}}{R_{DS(on)(25^\circ C)}}$$



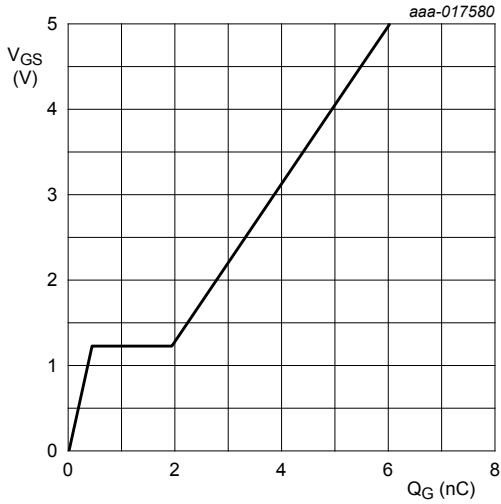
$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$
 (1) maximum values
 (2) typical values
 (3) minimum values

Fig. 13. Gate-source threshold voltage as a function of junction temperature



$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$
 (1) C_{iss}
 (2) C_{oss}
 (3) C_{rss}

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$I_D = 3\text{ A}$; $V_{DS} = 6\text{ V}$; $T_{amb} = 25\text{ }^\circ\text{C}$

Fig. 15. Gate-source voltage as a function of gate charge; typical values

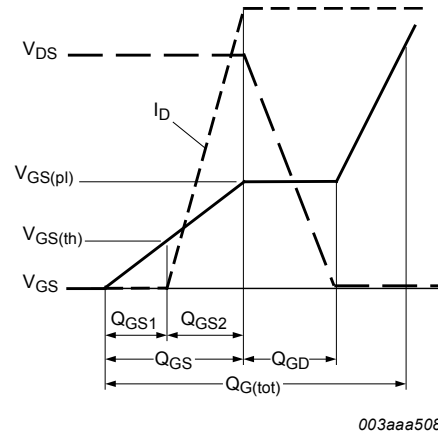
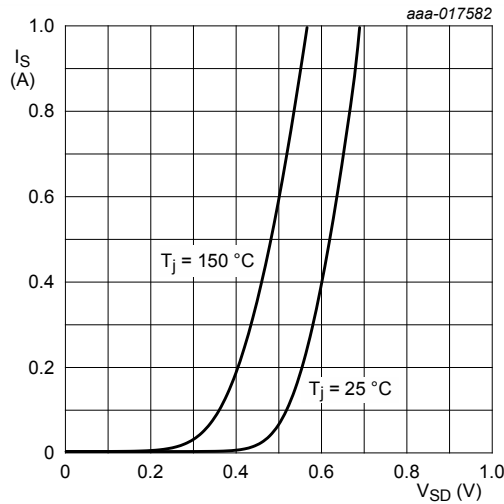


Fig. 16. MOSFET transistor: Gate charge waveform definitions



$V_{GS} = 0\text{ V}$

Fig. 17. Source current as a function of source-drain voltage; typical values

11. Test information

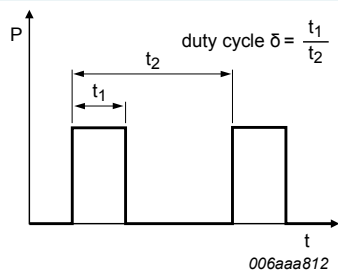


Fig. 18. Duty cycle definition

12. Package outline

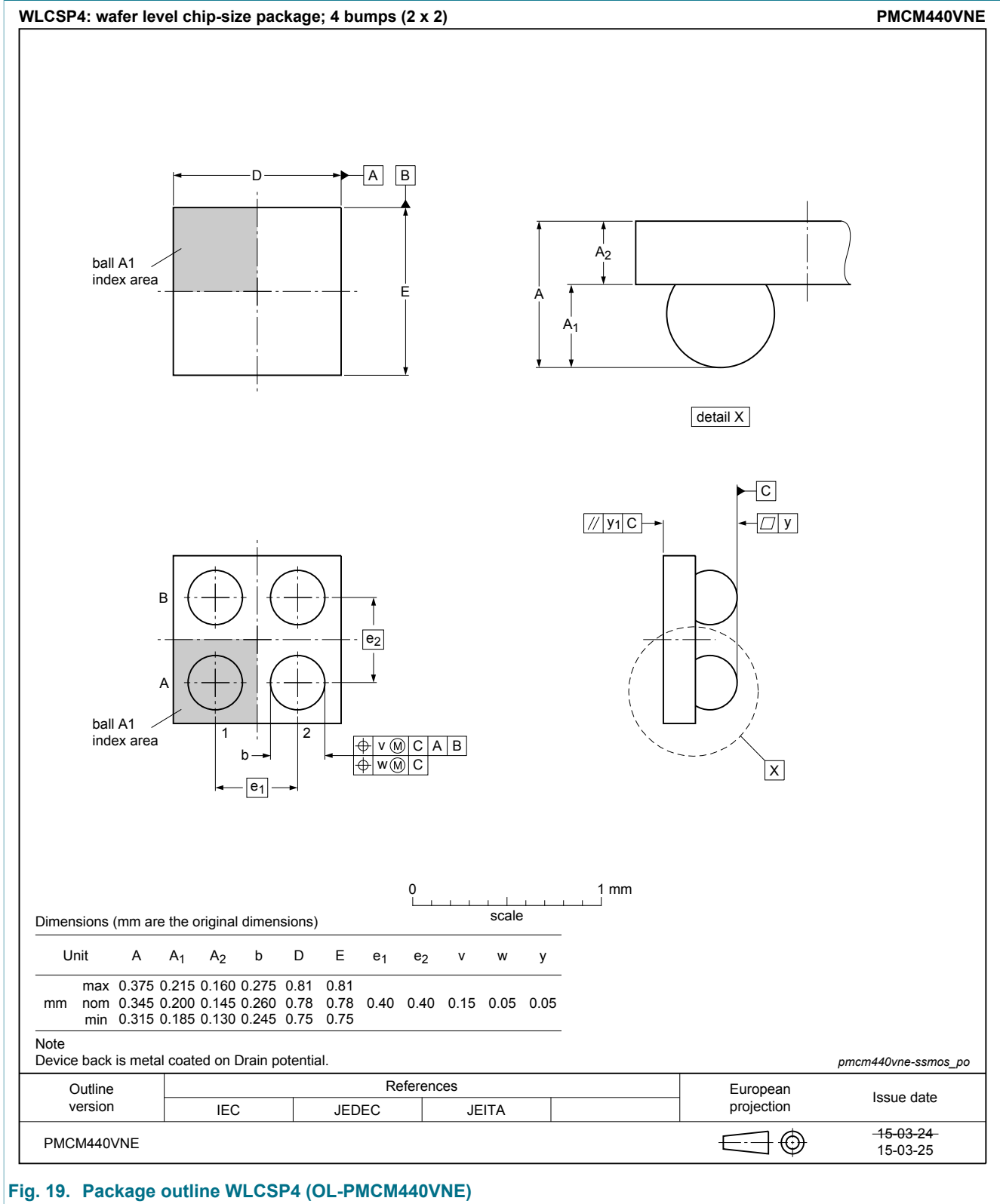


Fig. 19. Package outline WLCSP4 (OL-PMCM440VNE)

13. Soldering

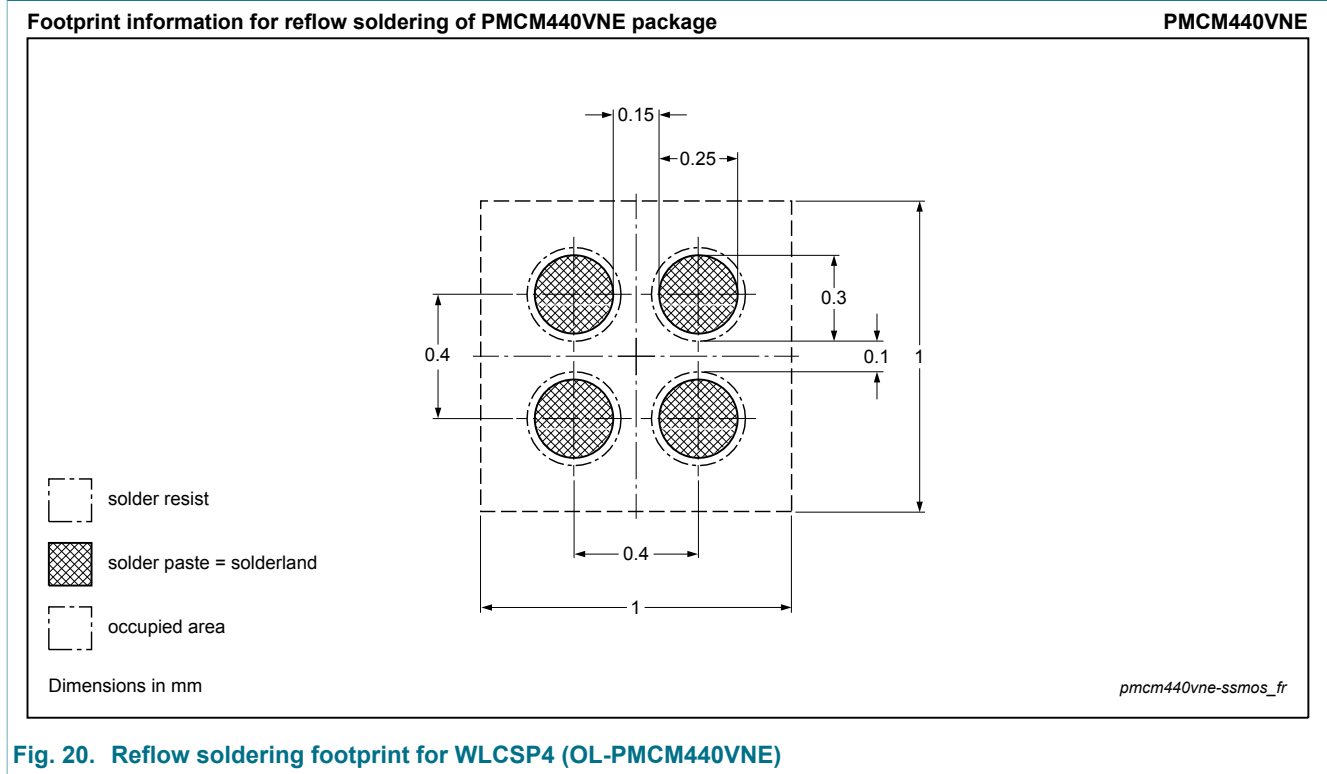


Fig. 20. Reflow soldering footprint for WLCSP4 (OL-PMCM440VNE)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMCM440VNE v.1	20150407	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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